ABSTRACT

A semiconductor device includes; a substrate including an active pattern, a channel pattern on the active pattern, the channel pattern including a plurality of spaced apart and vertically stacked semiconductor patterns, a source/drain pattern connected to the plurality of semiconductor patterns, a gate electrode on the plurality of semiconductor patterns, the gate electrode including a portion interposed between adjacent ones of the plurality of semiconductor patterns, and an inner spacer interposed between the portion of the gate electrode and the source/drain pattern, wherein the inner spacer is crystalline metal oxide is expressed by a formula (MO), wherein (O) is an oxygen atom, and (M) is a metal atom selected from a group consisting of Mg, Be, and Ga.

FIG. 6A